



6-Pin DIP Optoisolators Transistor Output

The 4N25, 4N26, 4N27 and 4N28 devices consist of a gallium arsenide infrared emitting diode optically coupled to a monolithic silicon phototransistor detector.

- Most Economical Optoisolator Choice for Medium Speed, Switching Applications
- Meets or Exceeds All JEDEC Registered Specifications
- **To order devices that are tested and marked per VDE 0884 requirements, the suffix "V" must be included at end of part number. VDE 0884 is a test option.**

Applications

- General Purpose Switching Circuits
- Interfacing and coupling systems of different potentials and impedances
- I/O Interfacing
- Solid State Relays

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
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INPUT LED

Reverse Voltage	V_R	3	Volts
Forward Current — Continuous	I_F	60	mA
LED Power Dissipation @ $T_A = 25^\circ\text{C}$ with Negligible Power in Output Detector Derate above 25°C	P_D	120	mW
		1.41	mW/ $^\circ\text{C}$

OUTPUT TRANSISTOR

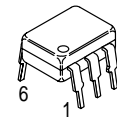
Collector–Emitter Voltage	V_{CEO}	30	Volts
Emitter–Collector Voltage	V_{ECO}	7	Volts
Collector–Base Voltage	V_{CBO}	70	Volts
Collector Current — Continuous	I_C	150	mA
Detector Power Dissipation @ $T_A = 25^\circ\text{C}$ with Negligible Power in Input LED Derate above 25°C	P_D	150	mW
		1.76	mW/ $^\circ\text{C}$

TOTAL DEVICE

Isolation Surge Voltage ⁽¹⁾ (Peak ac Voltage, 60 Hz, 1 sec Duration)	V_{ISO}	7500	Vac(pk)
Total Device Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	250 2.94	mW mW/ $^\circ\text{C}$
Ambient Operating Temperature Range	T_A	-55 to +100	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$
Soldering Temperature (10 sec, 1/16" from case)	T_L	260	$^\circ\text{C}$

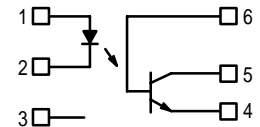
1. Isolation surge voltage is an internal device dielectric breakdown rating.
For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.

4N25
4N26
4N27
4N28



STANDARD THRU HOLE

SCHEMATIC



- PIN 1. LED ANODE
2. LED CATHODE
3. N.C.
4. EMITTER
5. COLLECTOR
6. BASE

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)⁽¹⁾

Characteristic	Symbol	Min	Typ ⁽¹⁾	Max	Unit
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INPUT LED

Forward Voltage ($I_F = 10\text{ mA}$)	$T_A = 25^\circ\text{C}$ $T_A = -55^\circ\text{C}$ $T_A = 100^\circ\text{C}$	V_F	— — —	1.15 1.3 1.05	1.5 — —	Volts
Reverse Leakage Current ($V_R = 3\text{ V}$)		I_R	—	—	100	μA
Capacitance ($V = 0\text{ V}$, $f = 1\text{ MHz}$)		C_J	—	18	—	pF

OUTPUT TRANSISTOR

Collector–Emitter Dark Current ($V_{CE} = 10\text{ V}$, $T_A = 25^\circ\text{C}$)	4N25,26,27 4N28	I_{CEO}	— —	1 1	50 100	nA
($V_{CE} = 10\text{ V}$, $T_A = 100^\circ\text{C}$)	All Devices	I_{CEO}	—	1	—	μA
Collector–Base Dark Current ($V_{CB} = 10\text{ V}$)		I_{CBO}	—	0.2	—	nA
Collector–Emitter Breakdown Voltage ($I_C = 1\text{ mA}$)		$V_{(BR)CEO}$	30	45	—	Volts
Collector–Base Breakdown Voltage ($I_C = 100\text{ }\mu\text{A}$)		$V_{(BR)CBO}$	70	100	—	Volts
Emitter–Collector Breakdown Voltage ($I_E = 100\text{ }\mu\text{A}$)		$V_{(BR)ECO}$	7	7.8	—	Volts
DC Current Gain ($I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$)		h_{FE}	—	500	—	—
Collector–Emitter Capacitance ($f = 1\text{ MHz}$, $V_{CE} = 0$)		C_{CE}	—	7	—	pF
Collector–Base Capacitance ($f = 1\text{ MHz}$, $V_{CB} = 0$)		C_{CB}	—	19	—	pF
Emitter–Base Capacitance ($f = 1\text{ MHz}$, $V_{EB} = 0$)		C_{EB}	—	9	—	pF

COUPLED

Output Collector Current ($I_F = 10\text{ mA}$, $V_{CE} = 10\text{ V}$)	4N25,26 4N27,28	I_C (CTR) ⁽²⁾	2 (20) 1 (10)	7 (70) 5 (50)	— —	mA (%)
Collector–Emitter Saturation Voltage ($I_C = 2\text{ mA}$, $I_F = 50\text{ mA}$)		$V_{CE(sat)}$	—	0.15	0.5	Volts
Turn–On Time ($I_F = 10\text{ mA}$, $V_{CC} = 10\text{ V}$, $R_L = 100\text{ }\Omega$) ⁽³⁾		t_{on}	—	2.8	—	μs
Turn–Off Time ($I_F = 10\text{ mA}$, $V_{CC} = 10\text{ V}$, $R_L = 100\text{ }\Omega$) ⁽³⁾		t_{off}	—	4.5	—	μs
Rise Time ($I_F = 10\text{ mA}$, $V_{CC} = 10\text{ V}$, $R_L = 100\text{ }\Omega$) ⁽³⁾		t_r	—	1.2	—	μs
Fall Time ($I_F = 10\text{ mA}$, $V_{CC} = 10\text{ V}$, $R_L = 100\text{ }\Omega$) ⁽³⁾		t_f	—	1.3	—	μs
Isolation Voltage ($f = 60\text{ Hz}$, $t = 1\text{ sec}$) ⁽⁴⁾		V_{ISO}	7500	—	—	Vac(pk)
Isolation Resistance ($V = 500\text{ V}$) ⁽⁴⁾		R_{ISO}	10^{11}	—	—	Ω
Isolation Capacitance ($V = 0\text{ V}$, $f = 1\text{ MHz}$) ⁽⁴⁾		C_{ISO}	—	0.2	—	pF

1. Always design to the specified minimum/maximum electrical limits (where applicable).
2. Current Transfer Ratio (CTR) = $I_C/I_F \times 100\%$.
3. For test circuit setup and waveforms, refer to Figure 11.
4. For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.

TYPICAL CHARACTERISTICS

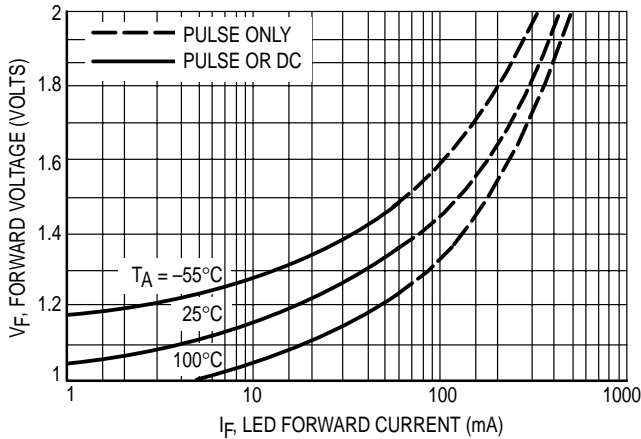


Figure 1. LED Forward Voltage versus Forward Current

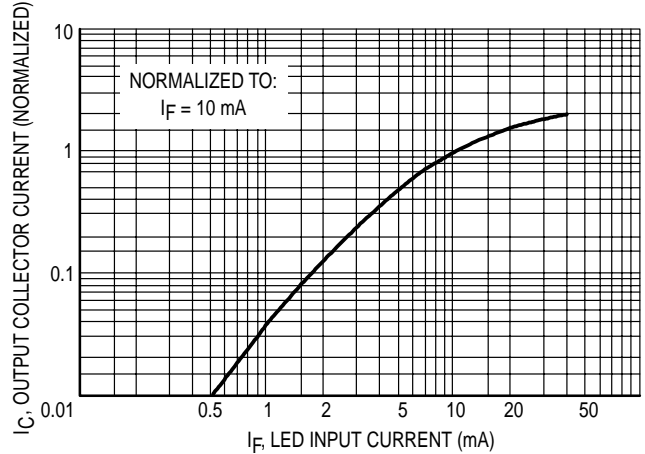


Figure 2. Output Current versus Input Current

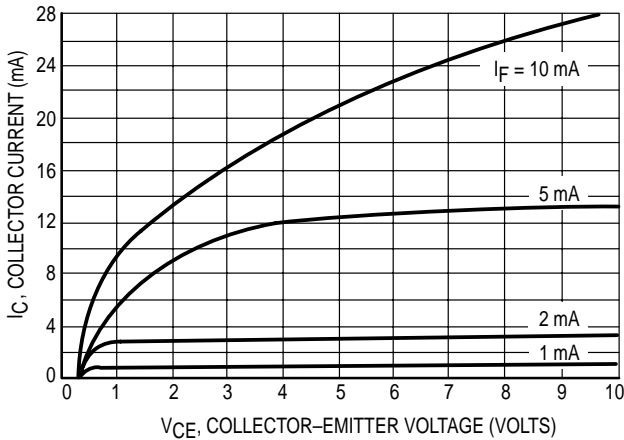


Figure 3. Collector Current versus Collector-Emitter Voltage

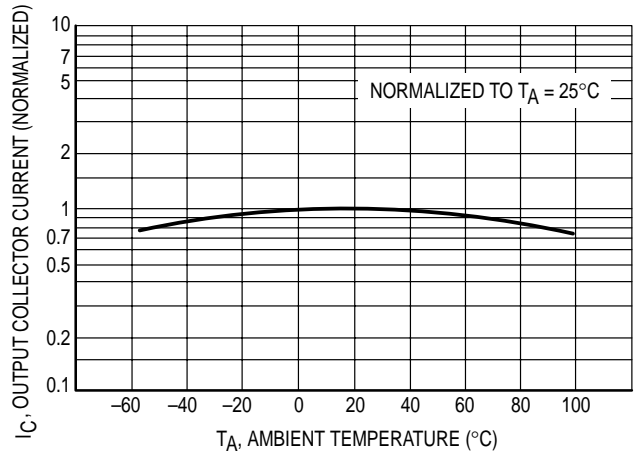


Figure 4. Output Current versus Ambient Temperature

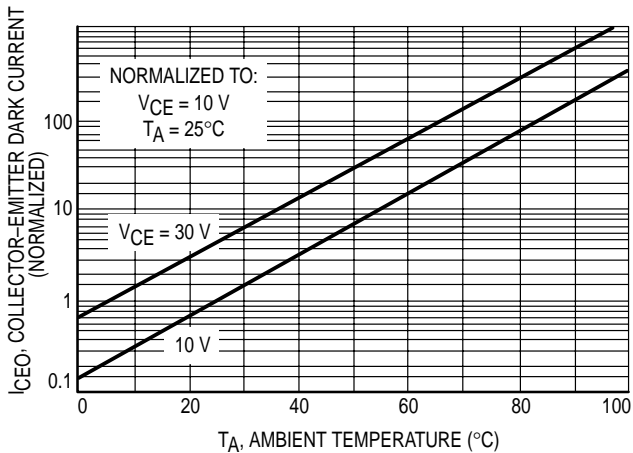


Figure 5. Dark Current versus Ambient Temperature

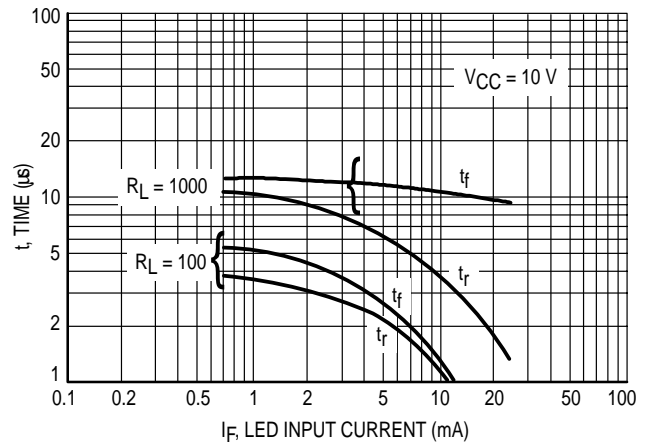


Figure 6. Rise and Fall Times (Typical Values)

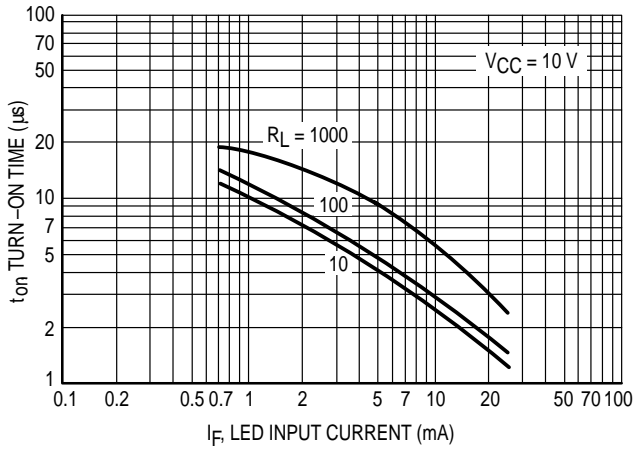


Figure 7. Turn-On Switching Times (Typical Values)

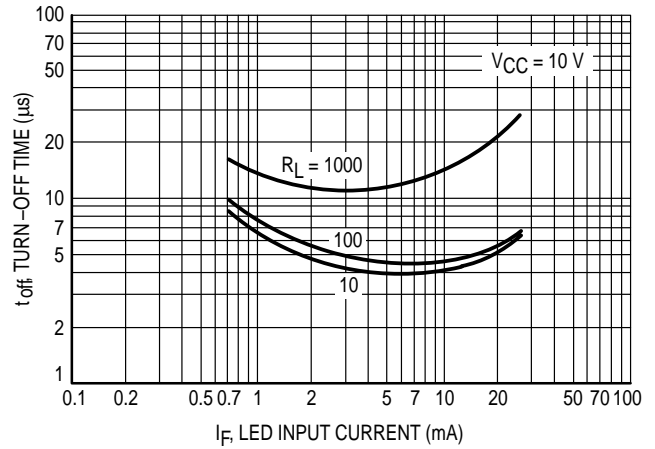


Figure 8. Turn-Off Switching Times (Typical Values)

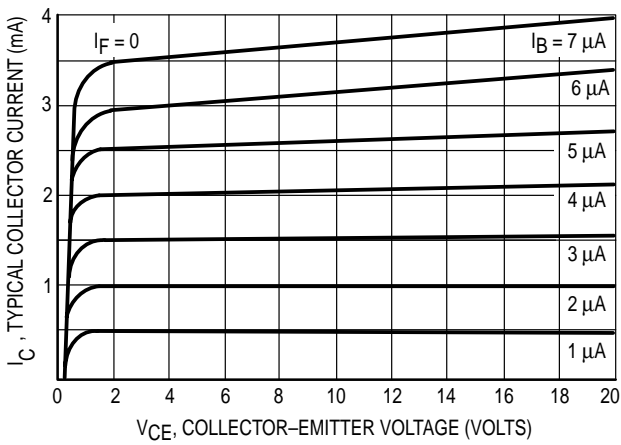


Figure 9. DC Current Gain (Detector Only)

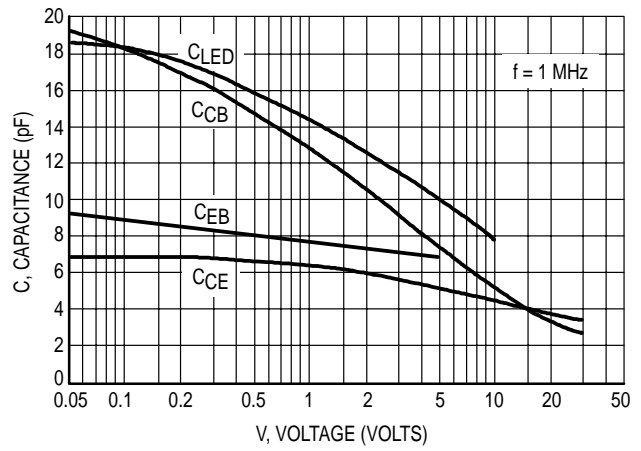


Figure 10. Capacitances versus Voltage

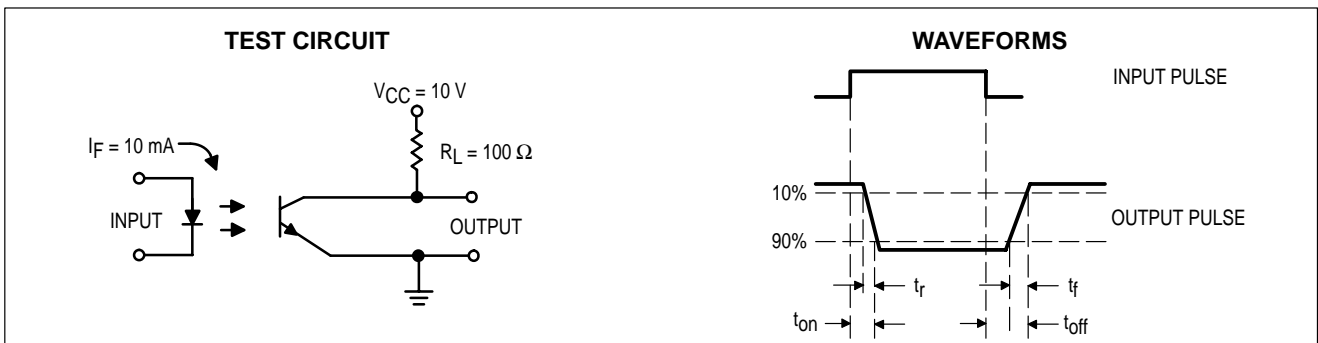
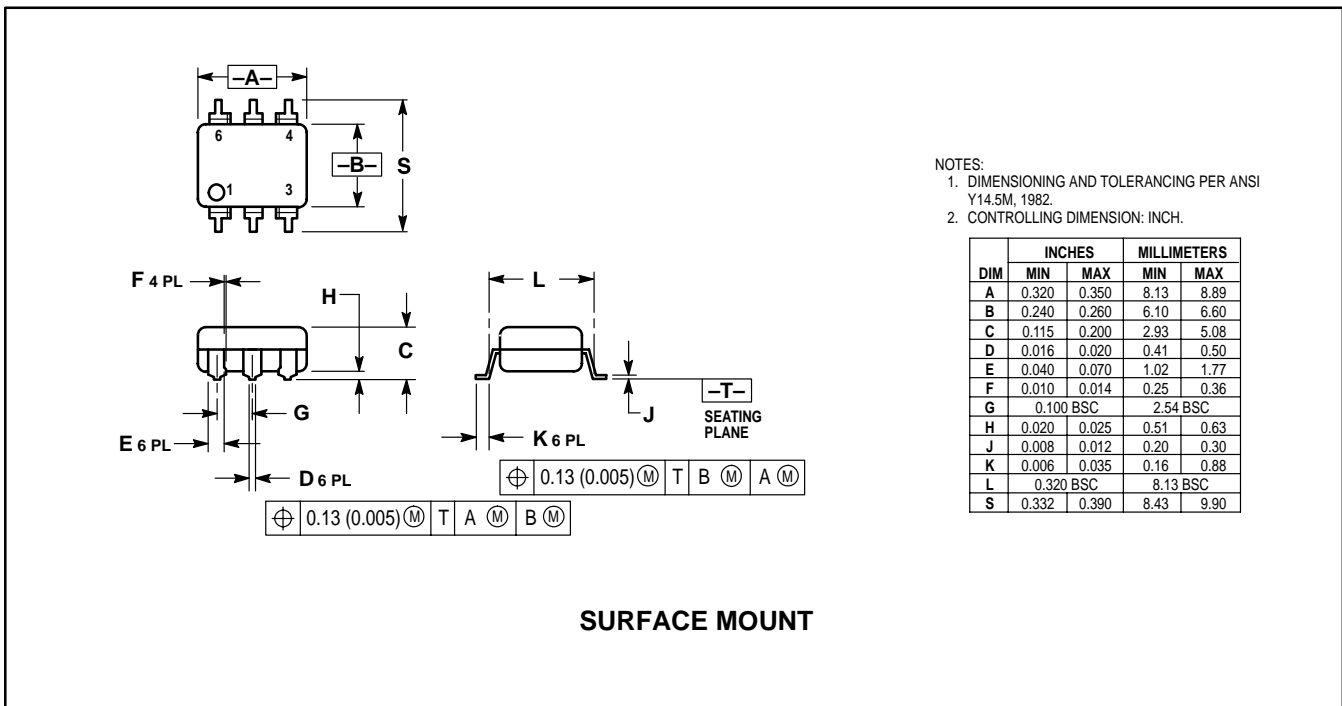
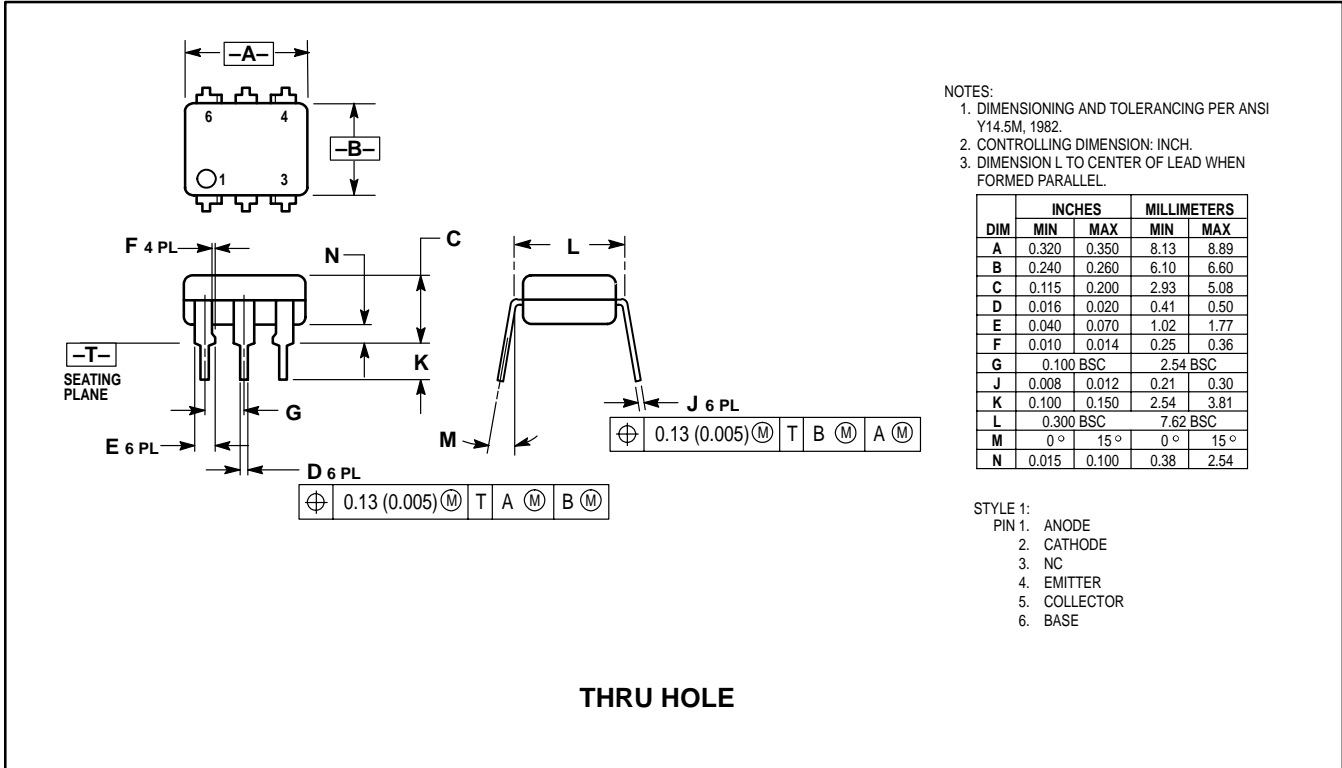
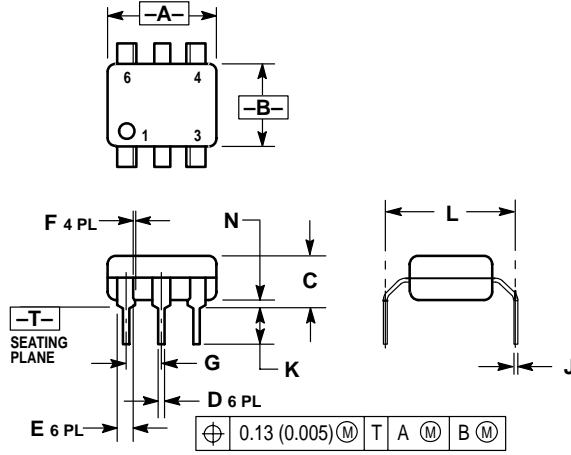


Figure 11. Switching Time Test Circuit and Waveforms

PACKAGE DIMENSIONS





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.320	0.350	8.13	8.89
B	0.240	0.260	6.10	6.60
C	0.115	0.200	2.93	5.08
D	0.016	0.020	0.41	0.50
E	0.040	0.070	1.02	1.77
F	0.010	0.014	0.25	0.36
G	0.100 BSC		2.54 BSC	
J	0.008	0.012	0.21	0.30
K	0.100	0.150	2.54	3.81
L	0.400	0.425	10.16	10.80
N	0.015	0.040	0.38	1.02

0.4" LEAD SPACING

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